

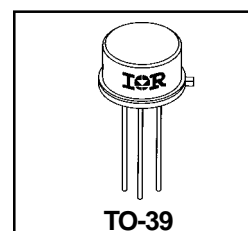
International IR Rectifier

RADIATION HARDENED POWER MOSFET THRU-HOLE (TO-39)

IRHF57130 100V, N-CHANNEL R5 TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	ID
IRHF57130	100K Rads (Si)	0.08Ω	11.7A
IRHF53130	300K Rads (Si)	0.08Ω	11.7A
IRHF54130	600K Rads (Si)	0.08Ω	11.7A
IRHF58130	1000K Rads (Si)	0.10Ω	11.7A



International Rectifier's R5™ technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm²)). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Ultra Low RDS(on)
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Ratings
- Dynamic dv/dt Ratings
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
ID @ VGS = 12V, TC = 25°C	Continuous Drain Current	11.7	A
ID @ VGS = 12V, TC = 100°C	Continuous Drain Current	7.4	
IDM	Pulsed Drain Current ①	47	
PD @ TC = 25°C	Max. Power Dissipation	25	W
	Linear Derating Factor	0.2	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	173	mJ
IAR	Avalanche Current ①	11.7	A
EAR	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.9	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Lead Temperature	300 (0.063 in./1.6mm from case for 10s)	
	Weight	0.98 (Typical)	g

For footnotes refer to the last page

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Pre-Irradiation

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
B _V DSS	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔB _V DSS/ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.12	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.08	Ω	V _{GS} = 12V, I _D = 7.4A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	8.7	—	—	S (Ω)	V _{DS} > 15V, I _{DS} = 7.4A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 80V, V _{GS} = 0V
		—	—	25		V _{DS} = 80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	50	nC	V _{GS} = 12V, I _D = 11.7A V _{DS} = 50V
Q _{gs}	Gate-to-Source Charge	—	—	7.4		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	20		
t _{d(on)}	Turn-On Delay Time	—	—	25	ns	V _{DD} = 50V, I _D = 11.7A R _G = 7.5Ω
t _r	Rise Time	—	—	100		
t _{d(off)}	Turn-Off Delay Time	—	—	35		
t _f	Fall Time	—	—	30		
L _S + L _D	Total Inductance	—	7.0	—	nH	Measured from Drain lead (6mm /0.25in. from package) to Source lead (6mm /0.25in. from package) with Source wires internally bonded from Source Pin to Drain Pad
C _{iss}	Input Capacitance	—	1038	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	362	—		
C _{rss}	Reverse Transfer Capacitance	—	45	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	11.7	A	T _J = 25°C, I _S = 11.7A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	47		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _J = 25°C, I _F = 11.7A, di/dt ≥ 100A/μs
t _{rr}	Reverse Recovery Time	—	—	202	ns	V _{DD} ≤ 25V ④
Q _{RR}	Reverse Recovery Charge	—	—	982	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	5.0	°C/W	Typical socket mount
R _{thJA}	Junction-to-Ambient	—	—	175		

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

Radiation Characteristics

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International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ^{⑤⑥}

	Parameter	Up to 600K Rads(Si) ¹		1000K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	100	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage ^④	2.0	4.0	1.5	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	—	10	μA	V _{DS} = 80V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ^④ On-State Resistance (TO-3)	—	0.064	—	0.08	Ω	V _{GS} = 12V, I _D = 7.4A
R _{DS(on)}	Static Drain-to-Source ^④ On-State Resistance (TO-39)	—	0.08	—	0.10	Ω	V _{GS} = 12V, I _D = 7.4A
V _{SD}	Diode Forward Voltage ^④	—	1.5	—	1.5	V	V _{GS} = 0V, I _S = 11.7A

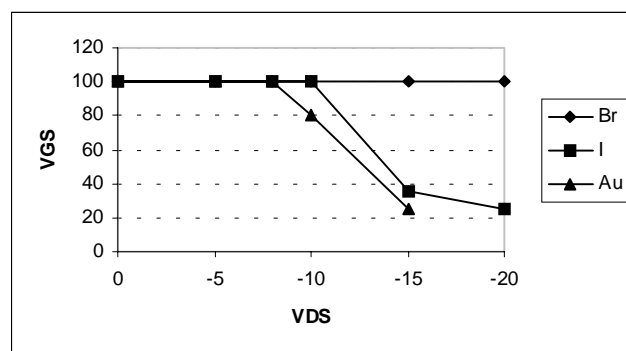
1. Part numbers IRHF57130, IRHF53130 and IRHF54130

2. Part number IRHF58130

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} = 0V	@V _{GS} = -5V	@V _{GS} = -10V	@V _{GS} = -15V	@V _{GS} = -20V
Br	36.7	309	39.5	100	100	100	100	100
I	59.8	341	32.5	100	100	100	35	25
Au	82.3	350	28.4	100	100	80	25	—


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

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Pre-Irradiation

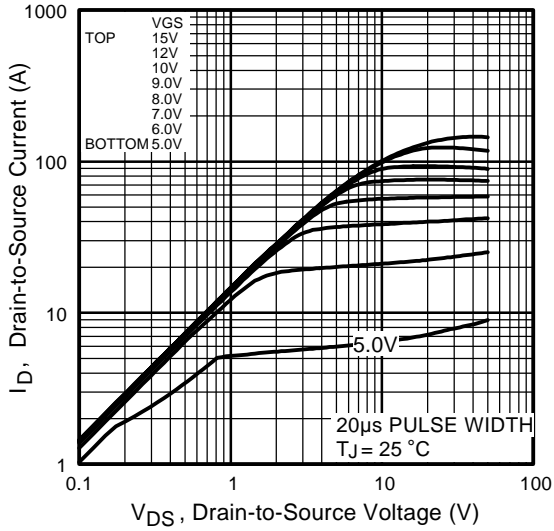


Fig 1. Typical Output Characteristics

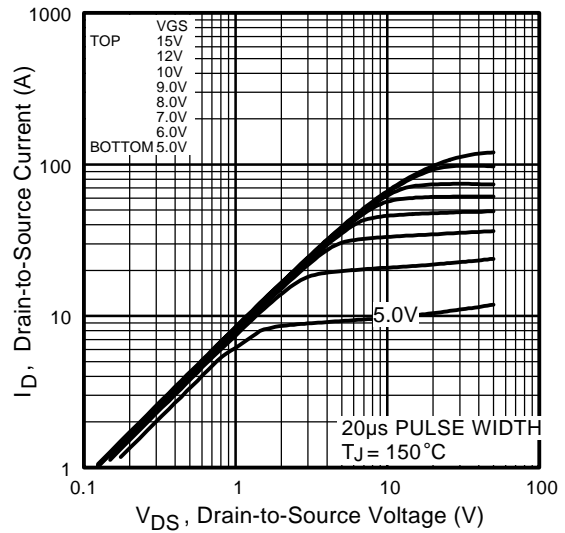


Fig 2. Typical Output Characteristics

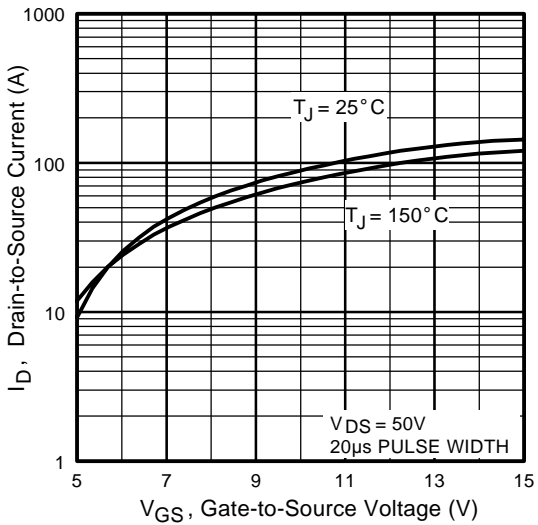


Fig 3. Typical Transfer Characteristics

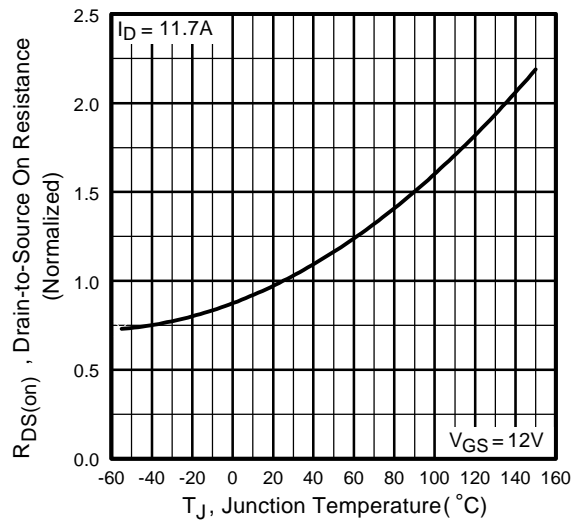


Fig 4. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

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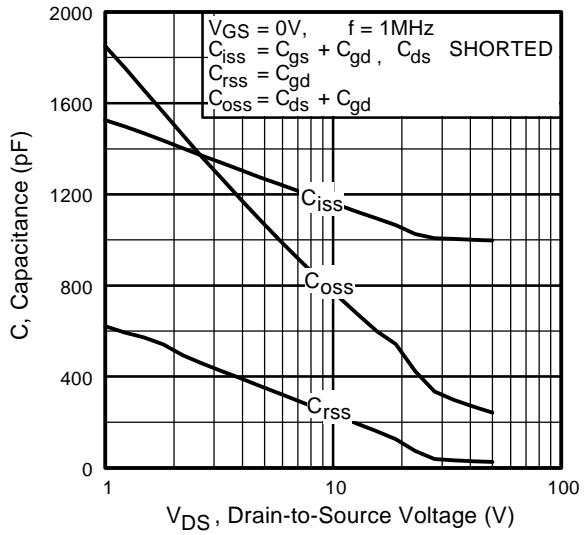


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

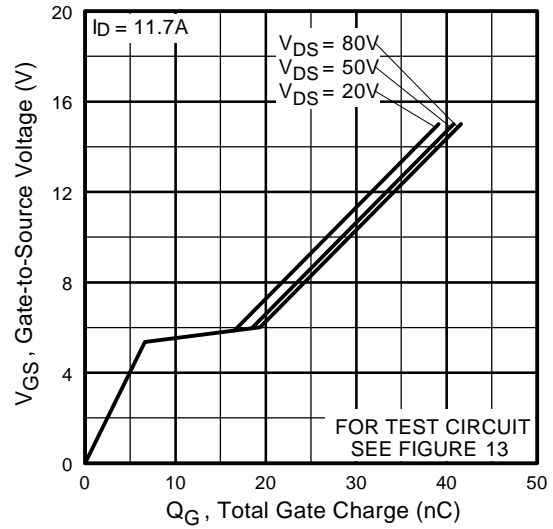


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

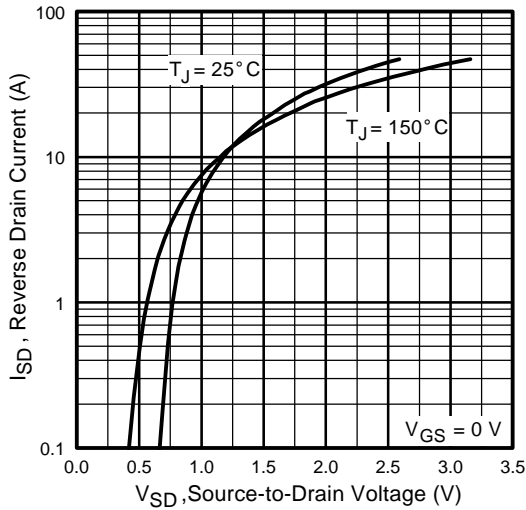


Fig 7. Typical Source-Drain Diode Forward Voltage

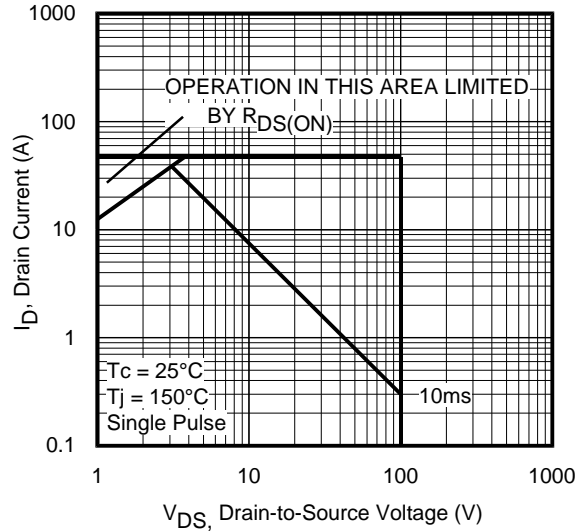


Fig 8. Maximum Safe Operating Area

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Pre-Irradiation

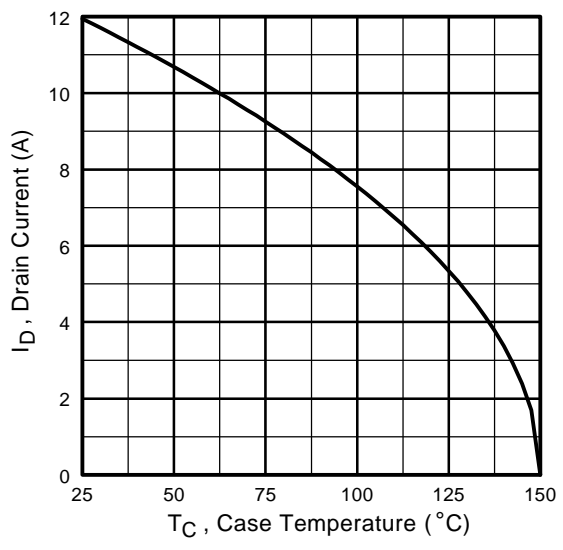


Fig 9. Maximum Drain Current Vs. Case Temperature

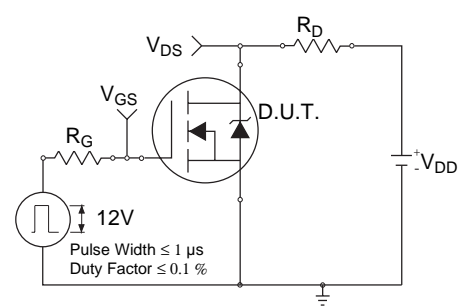


Fig 10a. Switching Time Test Circuit

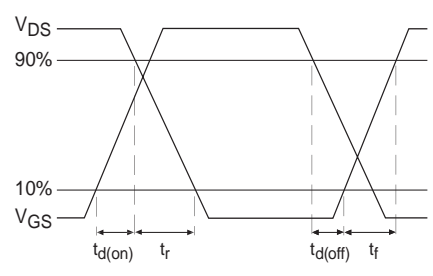


Fig 10b. Switching Time Waveforms

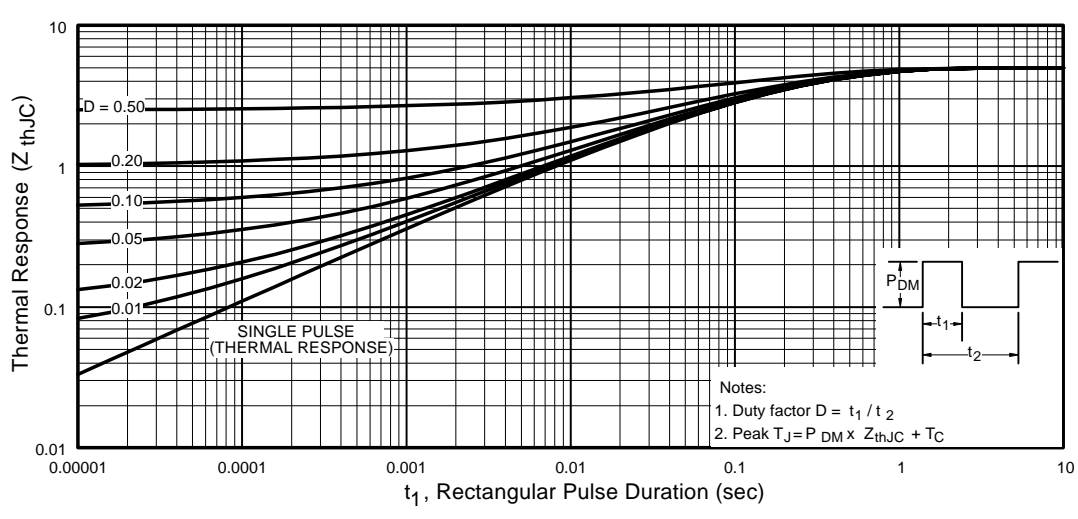


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

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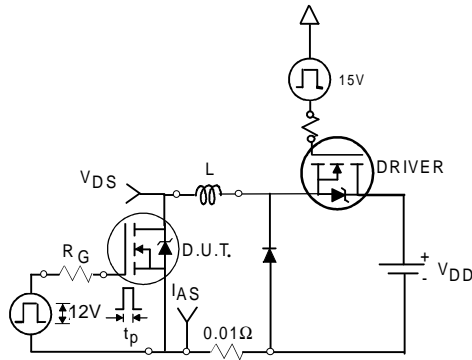


Fig 12a. Unclamped Inductive Test Circuit

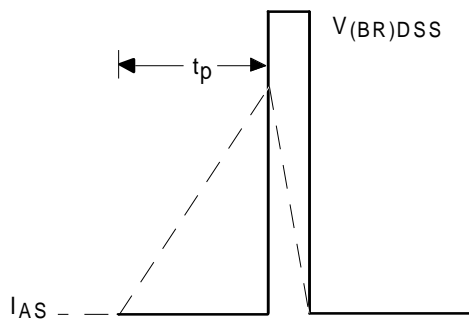


Fig 12b. Unclamped Inductive Waveforms

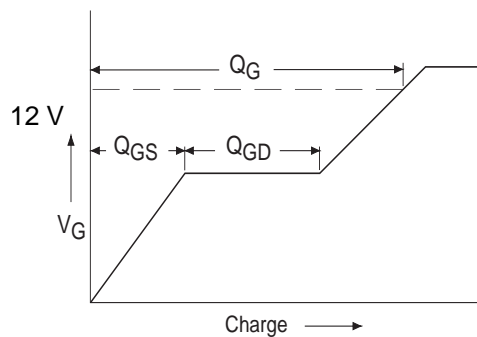


Fig 13a. Basic Gate Charge Waveform

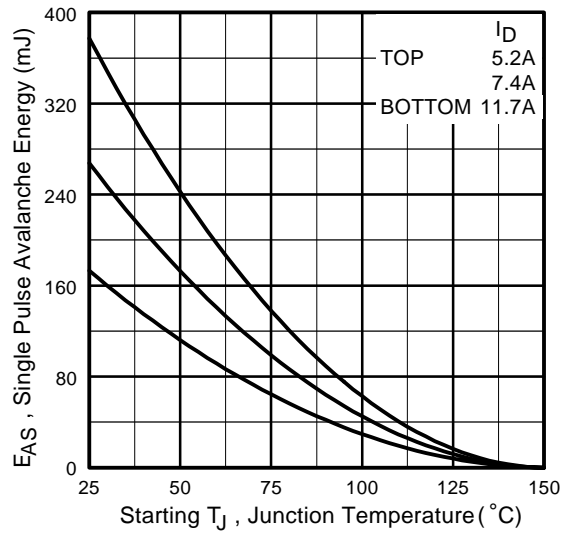


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

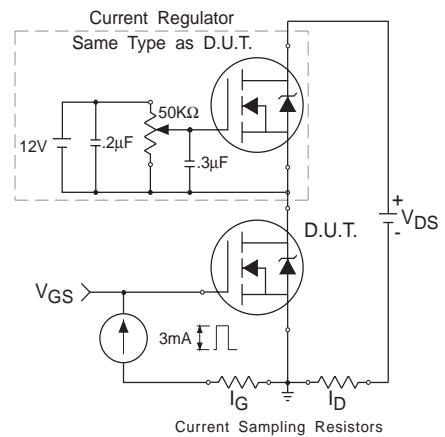


Fig 13b. Gate Charge Test Circuit

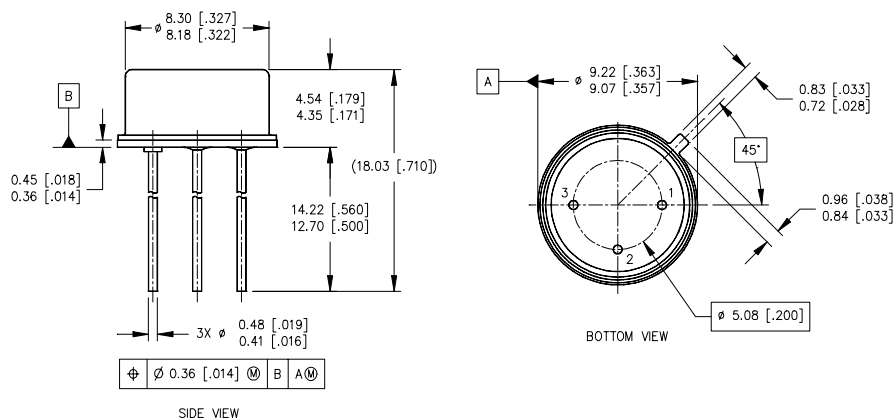
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Pre-Irradiation

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 50V$, starting $T_J = 25^\circ C$, $L = 2.53\text{ mH}$
Peak $I_L = 11.7A$, $V_{GS} = 12V$
- ③ $ISD \leq 11.7A$, $di/dt \leq 216A/\mu s$,
 $V_{DD} \leq 100V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300\ \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
80 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — TO-205AF (Modified TO-39)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME 14.5M-1994.
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: INCH.
4. CONFORMS TO JEDEC OUTLINE TO-205AF (TO-39).

LEGEND

- 1- SOURCE
- 2- GATE
- 3- DRAIN

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR EUROPEAN REGIONAL CENTER: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 OBL, UK Tel: ++ 44 (0)20 8645 8000

IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111

IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630

IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936

Data and specifications subject to change without notice. 3/00